

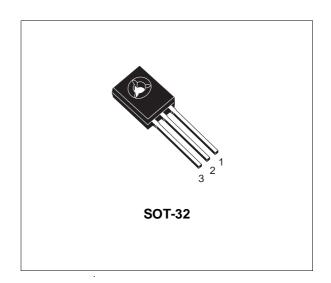


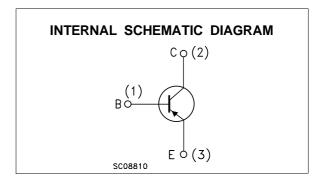
SILICON PNP TRANSISTOR

- SGS-THOMSON PREFERRED SALESTYPE
- PNP TRANSISTOR

DESCRIPTION

The BD234 is a silicon epitaxial-base PNP power transistor in Jedec SOT-32 plastic package inteded for use in medium power linear and switching applications.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I _E = 0)	-45	V
V_{CER}	Collector-Emitter Voltage (R _{BE} = 1KΩ)	-45	V
V_{CEO}	Collector-Emitter Voltage (I _B = 0)	-45	V
V_{EBO}	Emitter-Base Voltage (I _C = 0)	-5	V
Ic	Collector Current	-2	А
I _{CM}	Collector Peak Current	-6	А
P_{tot}	Total Dissipation at T _c ≤ 25 °C	25	W
T _{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

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THERMAL DATA

R _{thj-case} Thermal Resistance Junction-case	Max	5	°C/W
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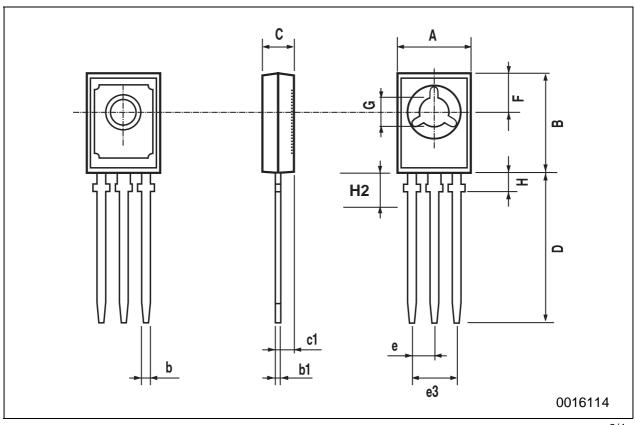
ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ ^{o}C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I _E = 0)	$V_{CB} = -45 \text{ V}$ $V_{CB} = -45 \text{ V}$ $T_{c} = 150 ^{\circ}\text{C}$			-0.1 -2	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = -5 V			-1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage	I _C = -100 mA	-45			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_C = -1 A$ $I_B = -0.1 A$			-0.6	V
V _{BE} *	Base-Emitter Voltage	$I_C = -1 A$ $V_{CE} = -2 V$			-1.3	V
h _{FE} *	DC Current Gain	$I_{C} = -150 \text{ mA}$ $V_{CE} = -2 \text{ V}$ $I_{C} = -1 \text{ A}$ $V_{CE} = -2 \text{ V}$	40 25			
f⊤	Transition frequency	I _C = -250 mA	3			MHz
h _{FE1} /h _{FE2} *	Matched Pairs	$I_{C} = -150 \text{ mA}$ $V_{CE} = -2 \text{ V}$		1.6		

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

SOT-32 (TO-126) MECHANICAL DATA

DIM.	mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	7.4		7.8	0.291		0.307
В	10.5		10.8	0.413		0.445
b	0.7		0.9	0.028		0.035
b1	0.49		0.75	0.019		0.030
С	2.4		2.7	0.040		0.106
c1	1.0		1.3	0.039		0.050
D	15.4		16.0	0.606		0.629
е		2.2			0.087	
e3	4.15		4.65	0.163		0.183
F		3.8			0.150	
G	3		3.2	0.118		0.126
Н			2.54			0.100
H2		2.15			0.084	



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